风光欣技术资料

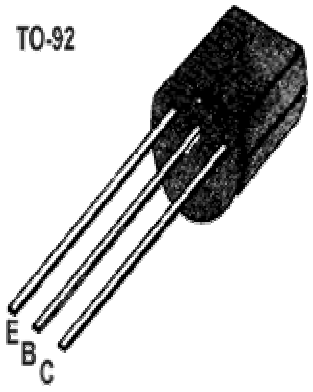
A44

—NPN silicon —

■■**APPLICATION**：High Voltage Amplifier.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	400	V
Collector-emitter voltage	V_{CEO}	400	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	300	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



■■**ELECTRICAL CHARACTERISTICS**（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	45		200		V_{CE}= 10 V，Ic= 10 mA
Collector Cut-off Current	I_{CBO}			0.1	μA	V_{CB}=400 V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.1	μA	V_{EB}= 4 V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	400			V	Ic= 0.1 mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	400			V	Ic= 1 mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	6			V	I_E= 0.1 mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.5	V	Ic= 10 mA，I_B= 1 mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$)			0.75	V	Ic= 50 mA，I_B= 5 mA
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.75	V	Ic= 10 mA，I_B= 1 mA
Gain bandwidth product	Ft	50			MHz	Ic= 10 mA，V_{CE}= 20 V，f = 100 MHz
Common Base Output Capacitance	Cob			7	PF	V_{CB}= 20 V，I_E=0，f = 1 MHz

■■h_{FE} **Classification**

Classification	
h_{FE}	45~200